

Ning Tang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

41
papers

546
citations

13
h-index

22
g-index

45
ext. papers

657
ext. citations

6.8
avg. IF

3.13
L-index

#	Paper	IF	Citations
41	Interfacial symmetry breaking induced spin-orbit coupling in wurtzite GaN nanowires. <i>Applied Physics Letters</i> , 2021 , 118, 122104	3.4	1
40	Spin dynamics in GaN/Al _{0.1} Ga _{0.9} N quantum well with complex band edge structure. <i>Applied Physics Letters</i> , 2021 , 118, 252107	3.4	2
39	Gate-tunable linear magnetoresistance in molybdenum disulfide field-effect transistors with graphene insertion layer. <i>Nano Research</i> , 2021 , 14, 1814-1818	10	3
38	High quality GaN-on-SiC with low thermal boundary resistance by employing an ultrathin AlGa _N buffer layer. <i>Applied Physics Letters</i> , 2021 , 118, 052104	3.4	7
37	Electrical Spin Injection into the 2D Electron Gas in AlN/GaN Heterostructures with Ultrathin AlN Tunnel Barrier. <i>Advanced Functional Materials</i> , 2021 , 31, 2009771	15.6	4
36	The in-plane anisotropy of the effective g factors in Al _{0.25} Ga _{0.75} N/GaN based quantum point contacts with narrow channels. <i>Applied Physics Letters</i> , 2020 , 116, 182101	3.4	1
35	Spin relaxation induced by interfacial effects in n-GaN/MgO/Co spin injectors.. <i>RSC Advances</i> , 2020 , 10, 12547-12553	3.7	2
34	Effective Manipulation of Spin Dynamics by Polarization Electric Field in InGa _N /Ga _N Quantum Wells at Room Temperature. <i>Advanced Science</i> , 2020 , 7, 1903400	13.6	4
33	Trapped Exciton-Polariton Condensate by Spatial Confinement in a Perovskite Microcavity. <i>ACS Photonics</i> , 2020 , 7, 327-337	6.3	21
32	Three Subband Occupation of the Two-Dimensional Electron Gas in Ultrathin Barrier AlN/GaN Heterostructures. <i>Advanced Functional Materials</i> , 2020 , 30, 2004450	15.6	4
31	High quality AlN film grown on a nano-concave-circle patterned Si substrate with an AlN seed layer. <i>Applied Physics Letters</i> , 2020 , 117, 022103	3.4	7
30	Investigation of carrier compensation traps in n-GaN drift layer by high-temperature deep-level transient spectroscopy. <i>Applied Physics Letters</i> , 2020 , 117, 112103	3.4	5
29	Epitaxy of Single-Crystalline GaN Film on CMOS-Compatible Si(100) Substrate Buffered by Graphene. <i>Advanced Functional Materials</i> , 2019 , 29, 1905056	15.6	33
28	Inversion Symmetry Breaking Induced Valley Hall Effect in Multilayer WSe ₂ . <i>ACS Nano</i> , 2019 , 13, 9325-9331	16.7	10
27	GaN-on-Si(100): Epitaxy of Single-Crystalline GaN Film on CMOS-Compatible Si(100) Substrate Buffered by Graphene (Adv. Funct. Mater. 42/2019). <i>Advanced Functional Materials</i> , 2019 , 29, 1970293	15.6	
26	Evidence of a strong perpendicular magnetic anisotropy in Au/Co/MgO/GaN heterostructures. <i>Nanoscale Advances</i> , 2019 , 1, 4466-4475	5.1	1
25	Vertical leakage induced current degradation and relevant traps with large lattice relaxation in AlGa _N /Ga _N heterostructures on Si. <i>Applied Physics Letters</i> , 2018 , 112, 032104	3.4	7

24	Epitaxial Single-Layer MoS on GaN with Enhanced Valley Helicity. <i>Advanced Materials</i> , 2018 , 30, 1703888	24	55
23	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. <i>Physical Review Letters</i> , 2018 , 121, 145505	7-4	27
22	Enhanced transport properties in InAlGaN/AlN/GaN heterostructures on Si (111) substrates: The role of interface quality. <i>Applied Physics Letters</i> , 2017 , 110, 172101	3-4	7
21	Magneto-transport Spectroscopy of the First and Second Two-dimensional Subbands in AlGaN/GaN Quantum Point Contacts. <i>Scientific Reports</i> , 2017 , 7, 42974	4-9	3
20	K- Γ crossover transition in the conduction band of monolayer MoS under hydrostatic pressure. <i>Science Advances</i> , 2017 , 3, e1700162	14-3	37
19	Local surface plasmon enhanced polarization and internal quantum efficiency of deep ultraviolet emissions from AlGaN-based quantum wells. <i>Scientific Reports</i> , 2017 , 7, 2358	4-9	13
18	Photon wavelength dependent valley photocurrent in multilayer MoS ₂ . <i>Physical Review B</i> , 2017 , 96,	3-3	10
17	Growth of high quality and uniformity AlGaN/GaN heterostructures on Si substrates using a single AlGaN layer with low Al composition. <i>Scientific Reports</i> , 2016 , 6, 23020	4-9	39
16	Hot electron induced non-saturation current behavior at high electric field in InAlN/GaN heterostructures with ultrathin barrier. <i>Scientific Reports</i> , 2016 , 6, 37415	4-9	5
15	Edge Dislocations Triggered Surface Instability in Tensile Epitaxial Hexagonal Nitride Semiconductor. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 34108-34114	9-5	5
14	High mobility AlGaN/GaN heterostructures grown on Si substrates using a large lattice-mismatch induced stress control technology. <i>Applied Physics Letters</i> , 2015 , 106, 142106	3-4	37
13	Generation of Rashba spin-orbit coupling in CdSe nanowire by ionic liquid gate. <i>Nano Letters</i> , 2015 , 15, 1152-7	11-5	28
12	Evidence of type-II band alignment in III-nitride semiconductors: experimental and theoretical investigation for In 0.17 Al 0.83 N/GaN heterostructures. <i>Scientific Reports</i> , 2014 , 4, 6521	4-9	13
11	Spin transport study in a Rashba spin-orbit coupling system. <i>Scientific Reports</i> , 2014 , 4, 4030	4-9	8
10	Identification of helicity-dependent photocurrents from topological surface states in Bi ₂ Se ₃ gated by ionic liquid. <i>Scientific Reports</i> , 2014 , 4, 4889	4-9	44
9	Formation of p-n-p junction with ionic liquid gate in graphene. <i>Applied Physics Letters</i> , 2014 , 104, 143102	3-4	8
8	Electronic properties of polycrystalline graphene under large local strain. <i>Applied Physics Letters</i> , 2014 , 104, 243108	3-4	12
7	Enhanced anisotropic effective g factors of an Al _{0.25} Ga _{0.75} N/GaN heterostructure based quantum point contact. <i>Nano Letters</i> , 2013 , 13, 4654-8	11-5	4

6	Effect of Grain Boundary Scattering on Electron Mobility of N-Polarity InN Films. <i>Applied Physics Express</i> , 2013 , 6, 021001	2.4	9
5	Temperature sensitive photoconductivity observed in InN layers. <i>Applied Physics Letters</i> , 2013 , 102, 072103	3.4	17
4	Fe-doped InN layers grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2012 , 101, 171905	3.4	4
3	Rashba and Dresselhaus spin-orbit coupling in GaN-based heterostructures probed by the circular photogalvanic effect under uniaxial strain. <i>Applied Physics Letters</i> , 2010 , 97, 181904	3.4	32
2	Influence of the illumination on the subband structure and occupation in Al _x Ga _{1-x} N/GaN heterostructures. <i>Applied Physics A: Materials Science and Processing</i> , 2009 , 96, 953-957	2.6	1
1	Zero-field spin splitting in Al _x Ga _{1-x} N/GaN heterostructures with various Al compositions. <i>Applied Physics Letters</i> , 2008 , 93, 172113	3.4	15